



# Z0103NA

4Q Triac

23 August 2013

Product data sheet

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring direct interfacing to logic ICs and low power gate drivers.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

## 4. Quick reference data

Table 1. Quick reference data

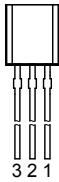
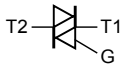
| Symbol                        | Parameter                            | Conditions  | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |   | -   | -   | 800 | V    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ;<br>$t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>   | -   | -   | 8   | A    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{\text{lead}} \leq 45\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ;<br><a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 1   | A    |
| <b>Static characteristics</b> |                                      |   |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                             | -   | -   | 3   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                             | -   | -   | 3   | mA   |



| Symbol | Parameter | Conditions  | Min | Typ | Max | Unit |
|--------|-----------|---|-----|-----|-----|------|
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | -   | -   | 3   | mA   |
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | -   | -   | 5   | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline   | Graphic symbol  |
|-----|--------|-----------------|--|---|
| 1   | T2     | main terminal 2 |  <p>TO-92 (SOT54)</p> |  <p>sym051</p> |
| 2   | G      | gate            |  |   |
| 3   | T1     | main terminal 1 |  |   |

## 6. Ordering information

Table 3. Ordering information

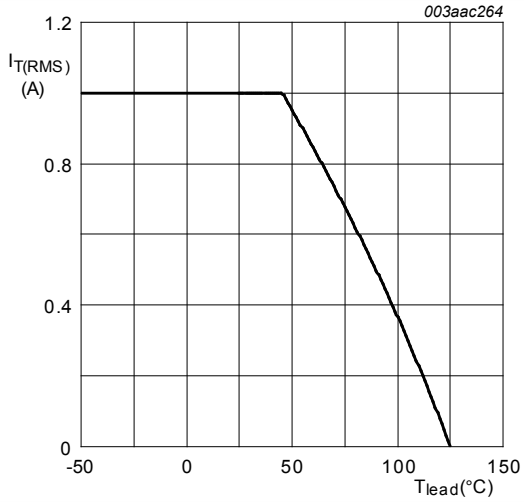
| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| Z0103NA     | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |

## 7. Limiting values

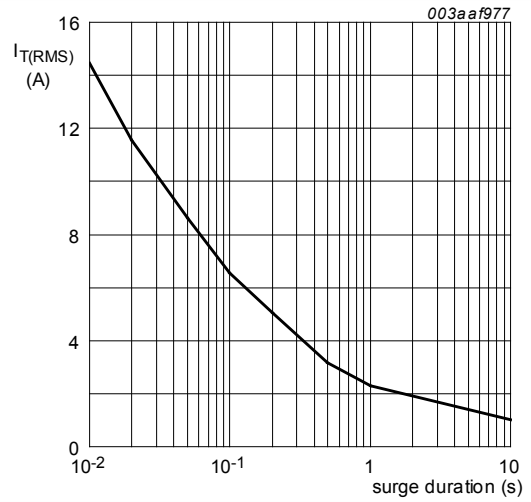
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions  | Min | Max  | Unit        |
|--------------|--------------------------------------|---|-----|------|-------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |   | -   | 800  | V           |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{lead} \leq 45\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | 1    | A           |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>   | -   | 8    | A           |
|              |                                      | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$   | -   | 8.5  | A           |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN  | -   | 0.32 | $A^2s$      |
| $di_T/dt$    | rate of rise of on-state current     | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $dI_G/dt = 0.1\text{ A}/\mu s$ ; T2+ G+                                     | -   | 50   | $A/\mu s$   |
|              |                                      | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $dI_G/dt = 0.1\text{ A}/\mu s$ ; T2+ G-                                     | -   | 50   | $A/\mu s$   |
|              |                                      | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $dI_G/dt = 0.1\text{ A}/\mu s$ ; T2- G-                                     | -   | 50   | $A/\mu s$   |
|              |                                      | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $dI_G/dt = 0.1\text{ A}/\mu s$ ; T2- G+                                     | -   | 20   | $A/\mu s$   |
| $I_{GM}$     | peak gate current                    |   | -   | 1    | A           |
| $P_{GM}$     | peak gate power                      |   | -   | 2    | W           |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period   | -   | 0.1  | W           |
| $T_{stg}$    | storage temperature                  |   | -40 | 150  | $^{\circ}C$ |
| $T_j$        | junction temperature                 |   | -   | 125  | $^{\circ}C$ |

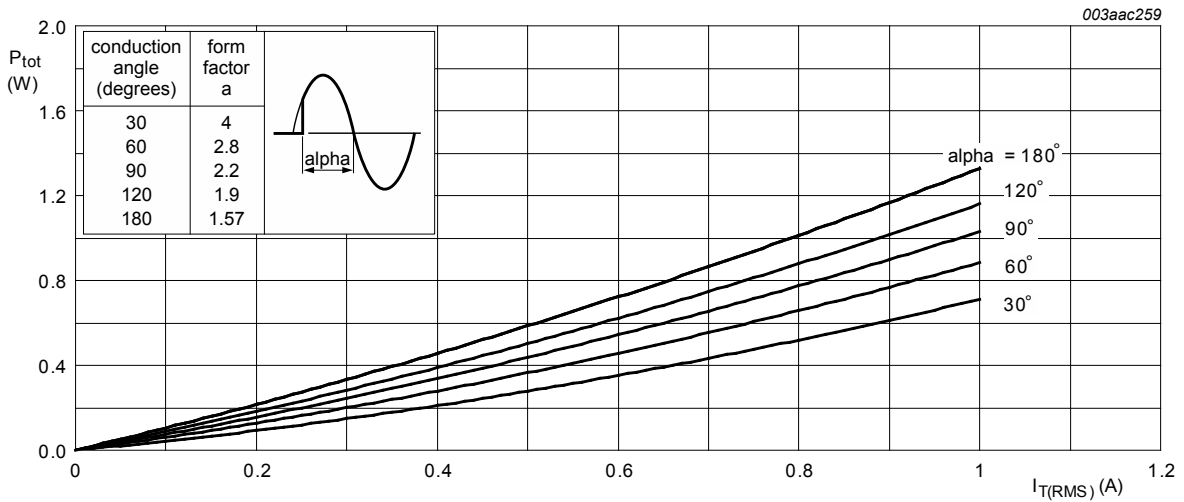


**Fig. 1. RMS on-state current as a function of lead temperature; maximum values**



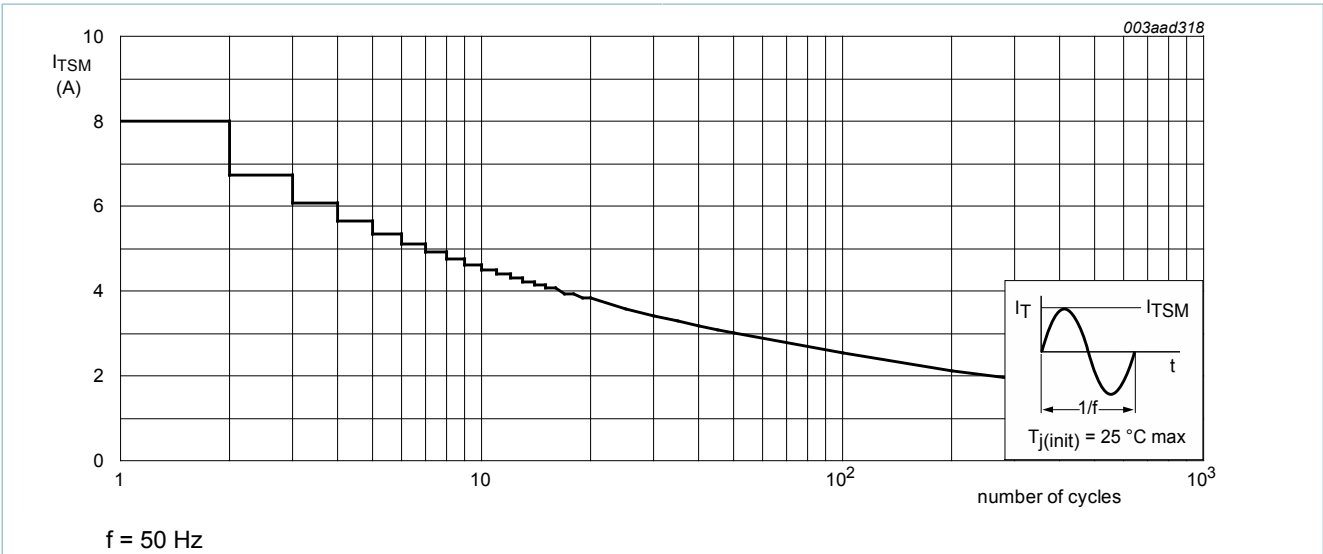
f = 50 Hz; T<sub>lead</sub> = 45 °C

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

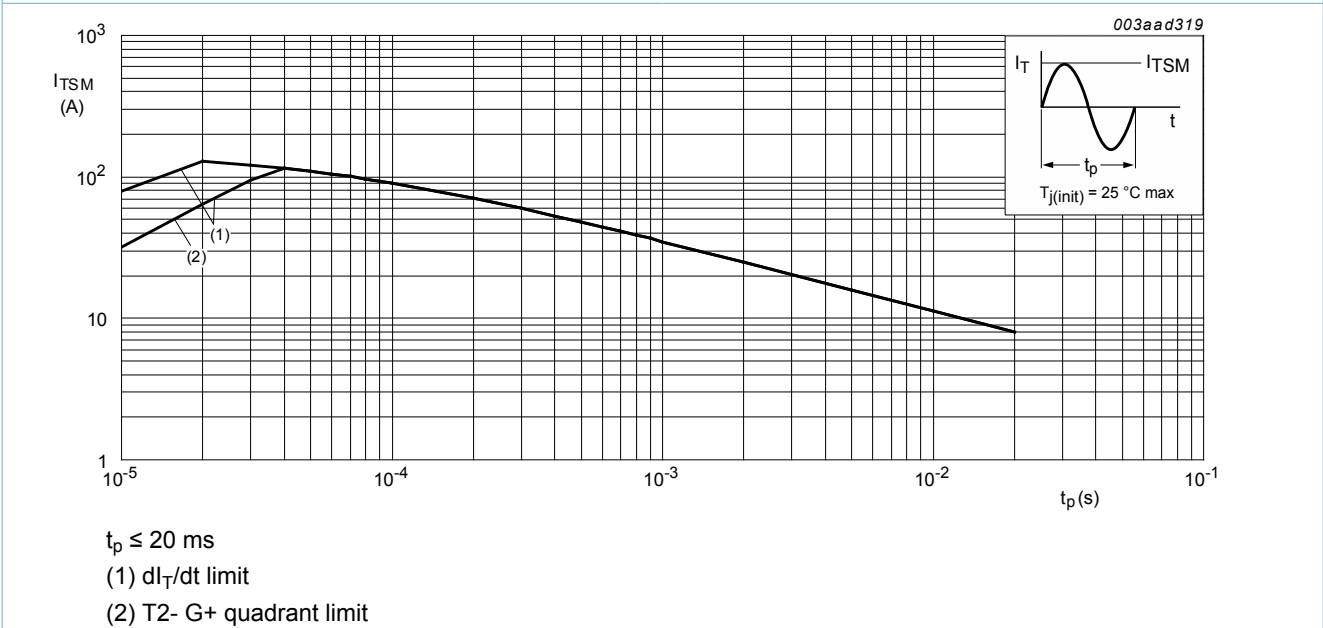


alpha = conduction angle

**Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values**



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



**Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values**

## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol           | Parameter                                   | Conditions  | Min | Typ | Max | Unit |
|------------------|---|---|-----|-----|-----|------|
| $R_{th(j-lead)}$ | thermal resistance from junction to lead    | full cycle; <a href="#">Fig. 6</a>                            | -   | -   | 60  | K/W  |
| $R_{th(j-a)}$    | thermal resistance from junction to ambient | full cycle; printed circuit board mounted; lead length = 4 mm | -   | 150 | -   | K/W  |

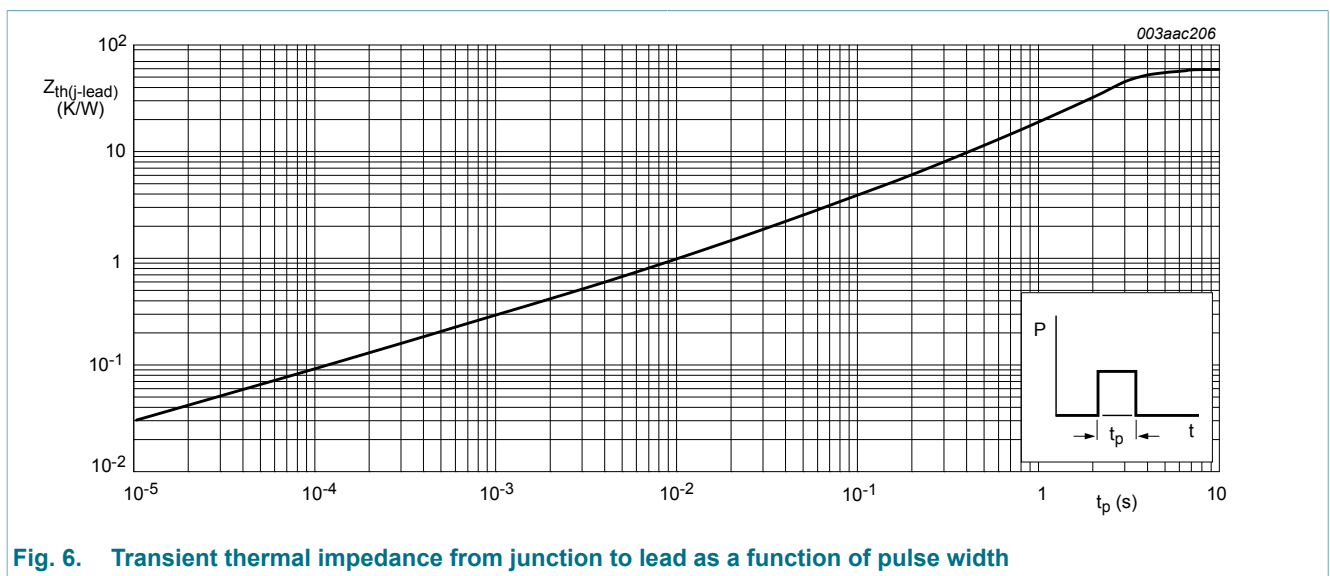
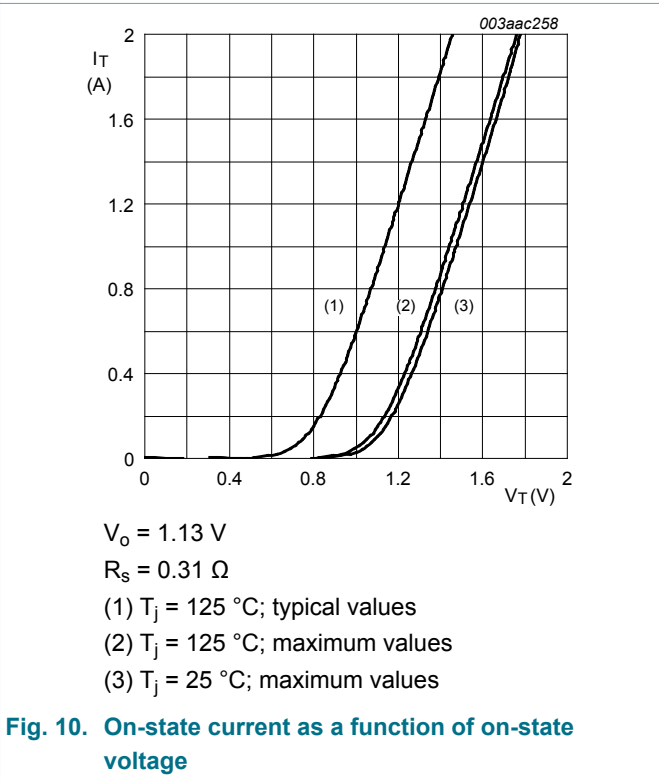
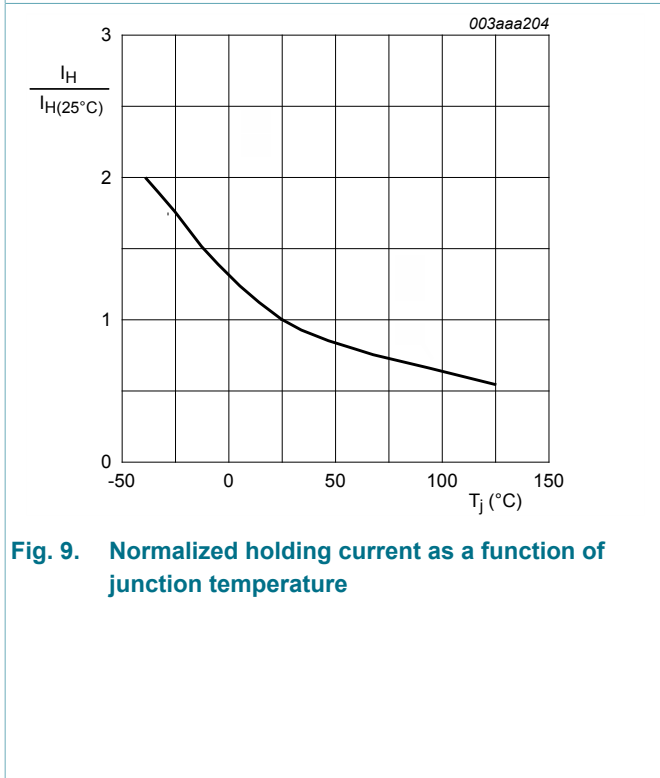
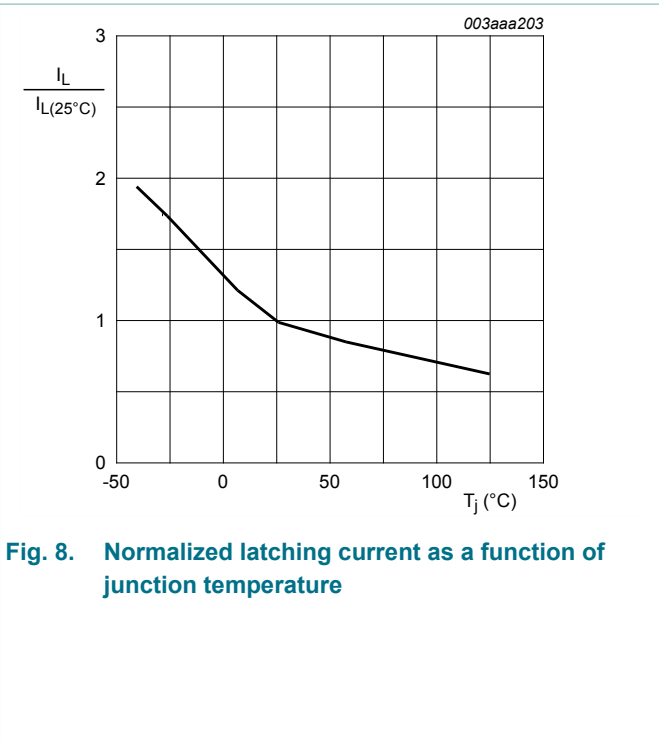
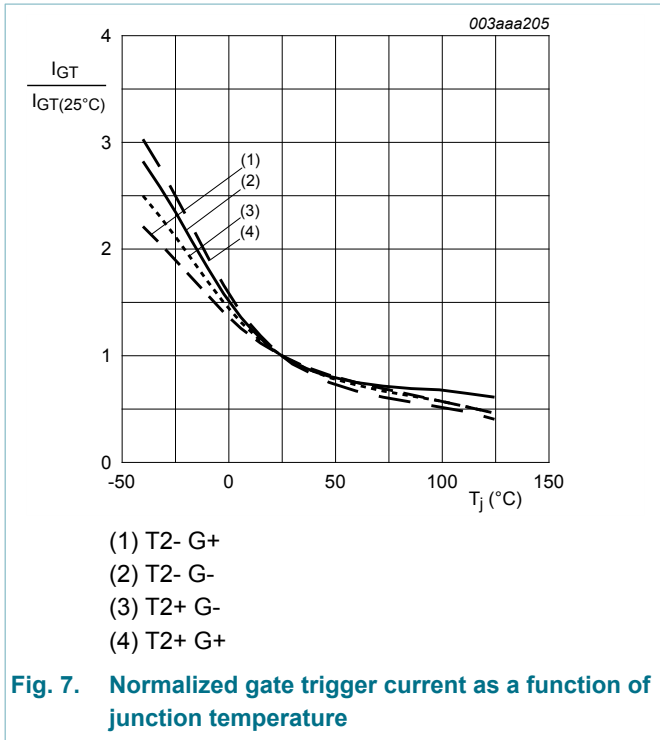


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------|
| <b>Static characteristics</b>  |                                       |  |     |     |     |      |
| I <sub>GT</sub>                | gate trigger current                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   | -   | -   | 3   | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   | -   | -   | 3   | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   | -   | -   | 3   | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>   | -   | -   | 5   | mA   |
| I <sub>L</sub>                 | latching current                      | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>   | -   | -   | 7   | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>   | -   | -   | 15  | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>   | -   | -   | 7   | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>   | -   | -   | 7   | mA   |
| I <sub>H</sub>                 | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>  | -   | -   | 7   | mA   |
| V <sub>T</sub>                 | on-state voltage                      | I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>  | -   | 1.3 | 1.6 | V    |
| V <sub>GT</sub>                | gate trigger voltage                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C;<br><a href="#">Fig. 11</a>  | -   | -   | 1   | V    |
|                                |                                       | V <sub>D</sub> = 800 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C;<br><a href="#">Fig. 11</a>  | 0.2 | -   | -   | V    |
| I <sub>D</sub>                 | off-state current                     | V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C  | -   | -   | 0.5 | mA   |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |      |
| dV <sub>D</sub> /dt            | rate of rise of off-state voltage     | V <sub>DM</sub> = 536 V; T <sub>j</sub> = 110 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a> | 10  | -   | -   | V/μs |
| dV <sub>com</sub> /dt          | rate of change of commutating voltage | V <sub>D</sub> = 400 V; T <sub>j</sub> = 110 °C; dI <sub>com</sub> /dt = 0.44 A/ms; I <sub>T</sub> = 1 A; gate open circuit                                      | 0.5 | -   | -   | V/μs |





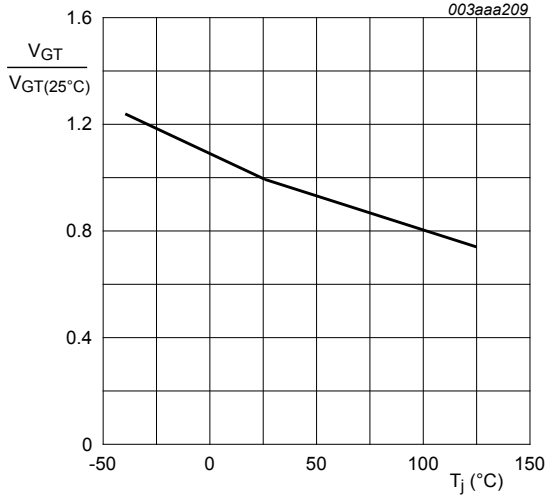


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

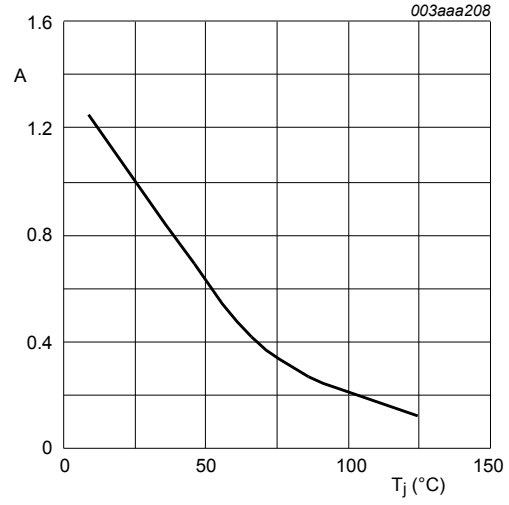


Fig. 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

$$A = \frac{dV_{D(T_j \text{ } ^\circ\text{C})} / dt}{dV_{D(25 \text{ } ^\circ\text{C})} / dt}$$

10. Package outline

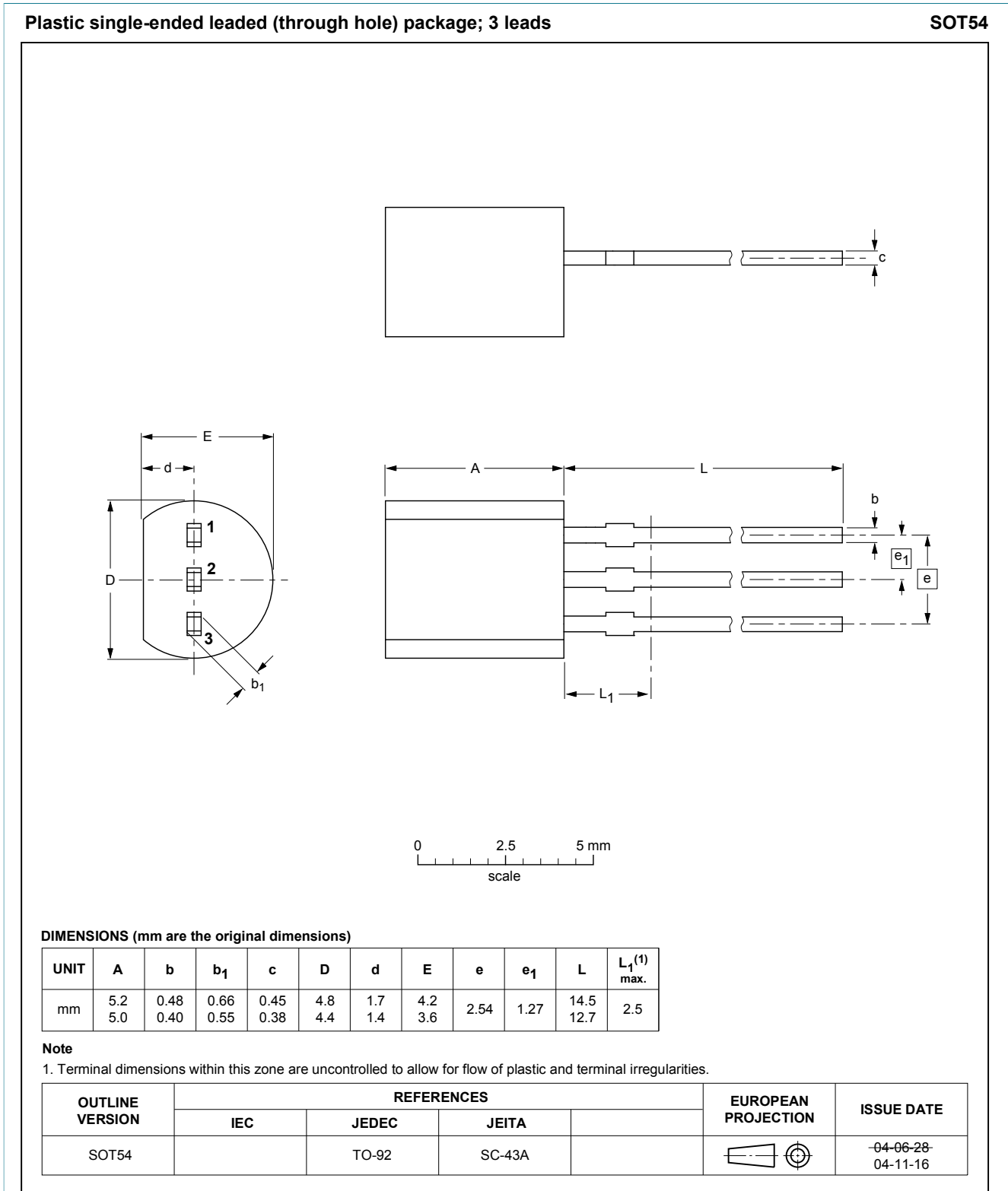


Fig. 13. Package outline TO-92 (SOT54)

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|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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